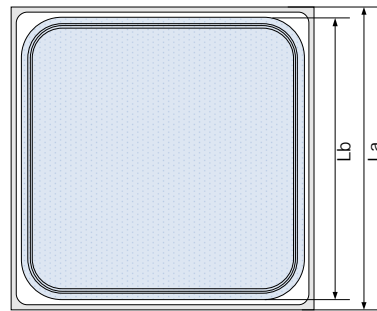


2SB035100ML SCHOTTKY BARRIER DIODE CHIPS
DESCRIPTION

- Ø 2SB035100ML is a schottky barrier diode chips fabricated in silicon epitaxial planar technology;
- Ø Low power losses, high efficiency;
- Ø Guard ring construction for transient protection;
- Ø High ESD capability;
- Ø High surge capability;
- Ø Packaged products are widely used in switching power suppliers, polarity protection circuits and other electronic circuits;
- Ø Chip Size: 350 μ m X 350 μ m;
- Ø Chip Thickness: 155 \pm 20 μ m


Chip Topography and Dimensions
La: Chip Size: 350 μ m;
Lb: Pad Size: 300 μ m;
ORDERING SPECIFICATIONS

Product Name	Specification
2SB035100MLJY	For Au and AlSi wire bonding package

ABSOLUTE MAXIMUM RATINGS

Parameters	Symbol	Ratings	Unit
Maximum Repetitive Peak Reverse Voltage	VRRM	100	V
Average Forward Rectified Current	IFAV	75	mA
Peak Forward Surge Current@10ms	IFSM	750	mA
Maximum Operation Junction Temperature	TJ	125	$^{\circ}$ C
Storage Temperature Range	TSTG	-40~125	$^{\circ}$ C

ELECTRICAL CHARACTERISTICS (Tamb=25 $^{\circ}$ C)

Parameters	Symbol	Test Conditions	Min.	Max.	Unit
Reverse Voltage	VBR	IR=100 μ A	100	--	V
Forward Voltage	VF1	IF=0.1mA	--	0.25	V
	VF2	IF=10mA	--	0.45	V
	VF3	IF=250mA	--	1	V
Reverse Current	IR	VR=50V	--	2	μ A
	IR	VR=75V	--	5	μ A